

(19)
(12)

(KR)
(A)

(51) Int. Cl.⁷
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(11)
(43)

2003-0078361
2003 10 08

(21) 10-2002-0017361
(22) 2002 03 29

(71) . 20

(72) 410-2 202 303

(74)
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(54)

, ' 가 ,
, ' 가

3b

(Eximer laser),

(Indium Tin Oxide)

1a .

1b 1a l l' .

2a 2f .

3a 3c .

4 1 .

1b (1) (11) 가 FT) (13) , (2), (12) (5b) , (7) (5a)(5) 1 (9) (8) (9) (1) (2) (11) (5a)(5b) (12) (13) (17a) (1) (12) (12) (3) / (7)(Thin Film Transistor ; T

2 (10) (14) (1) (14) (3) (7) (15) , 1 (9) (17) (23) (16) 1 (9) 2 (10) (16) (10) , (9) 2 (10) (15) , (1) (14) (3) (7) (15) , (16) 1 (9) 2 (10) (16) (10) , (9) 2 (10) (15) , (1) (9) 2 (10) 가

osition) (Cleaning) , PR(Photo Resistor) , UV , (Patterning) (Develop), (Thin Film D (Photolithography) (Etching), PR (Strip)

2a 2f (8a) PR(20) (8a) (Baking) (13) , (8) , (8a) PR(20) (21) (22) (8a) , PR(20) , PR(20) (8a) PR(20)

(8a) (8a) (13) (8) (8a) , PR , , , PR

가 , mer laser) (Exi

가

(Eximer laser)

3a 3d
 3a (102) (102) (109) (109) (111) (111)
 12) (102) (105a) (111) (105b) (112) (105a) (105b) (105b) (113) (105b) (113) (105b)
 8a) (113) (121) (108a) (122) (108a) (122) (122) (122) (10) (108a)
 (108b) (108a) 200 (122) (108a)
 (108b) (108a) (108a) (108a) (108a)
 (108a) (108b) (108a)
 (108a)
 , 10% (108b) 1 (108a)

()	(/m)	(/sec)	
25	30	7.9	0.0
30	30	11.1	0.0
35	30	14.3	0.0
65	30		1.2

1 (108a) (108b)
 가 1
 4 (108a)
 (108b)

(122)

(108a)

(108b)

(108a)
(122)

(108b)

(113)

(108a)

(108a)

(108a)

(108a)

(113)
(122)
(108b)
(108a)

(108a)

가

(57)

1.

가

가

2.

1

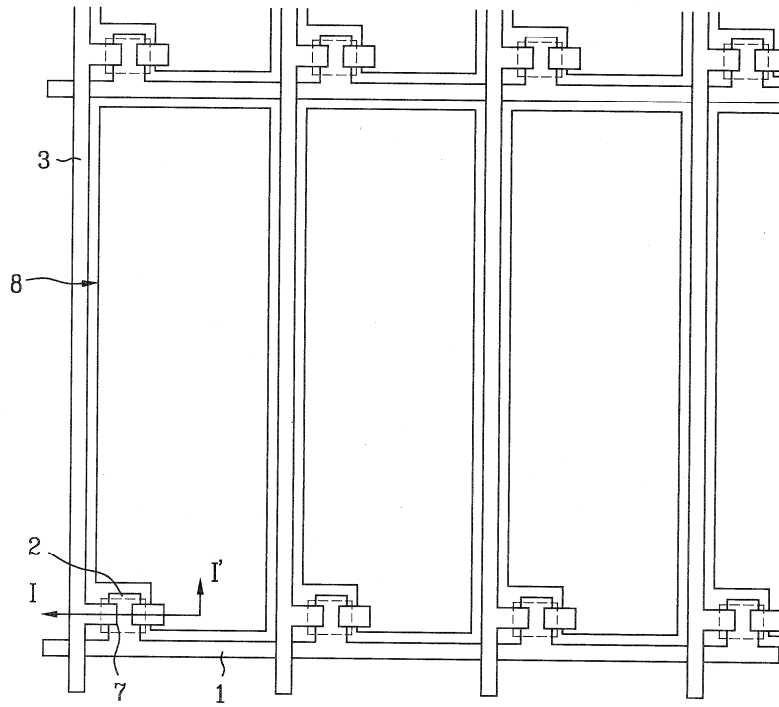
3.

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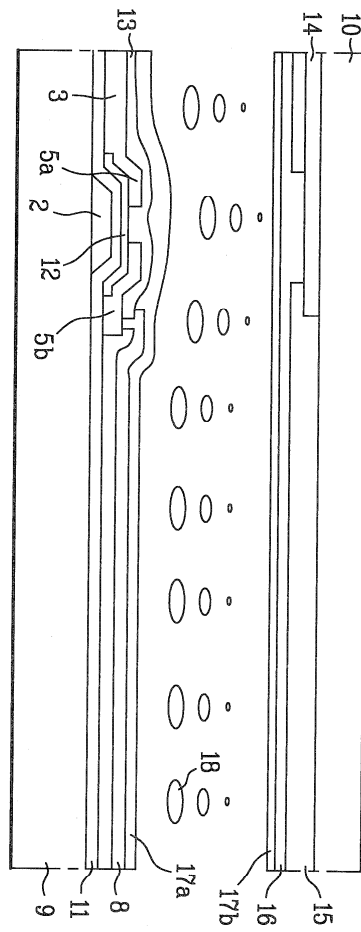
4.

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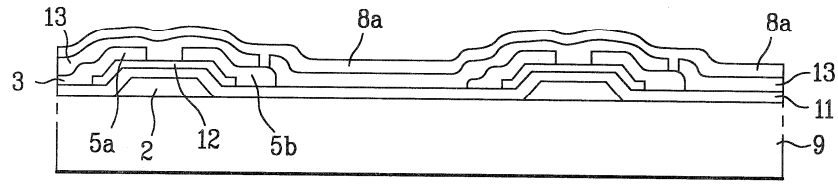
1a



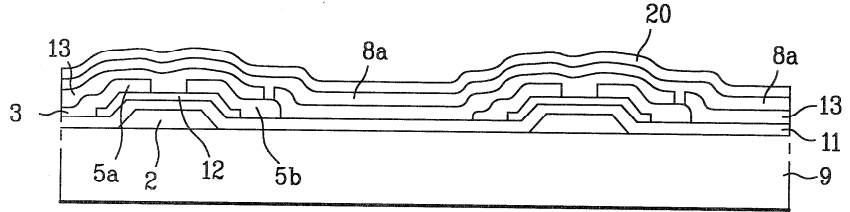
1b



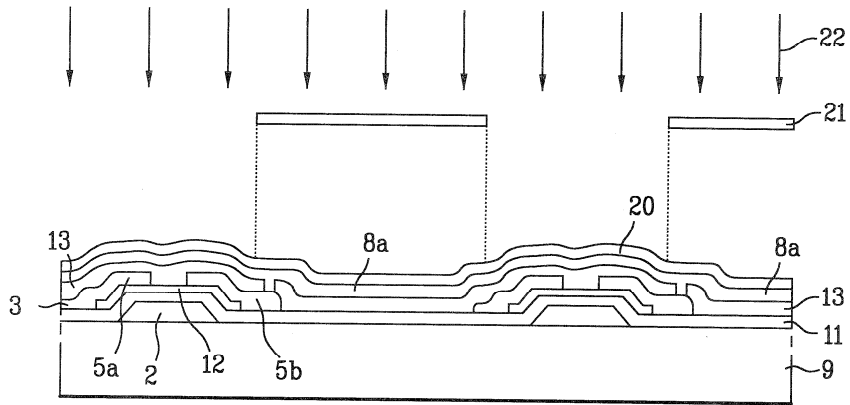
2a



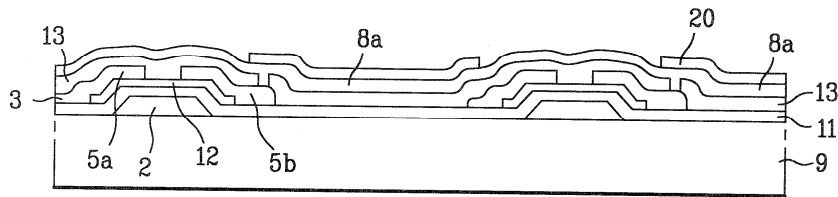
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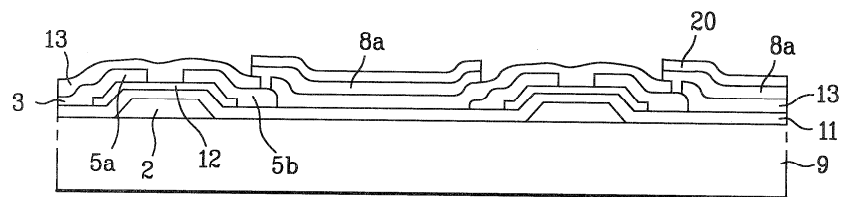
2c



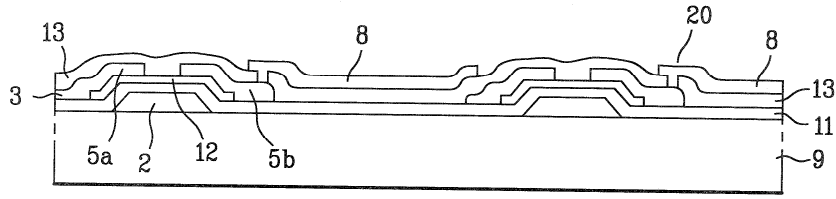
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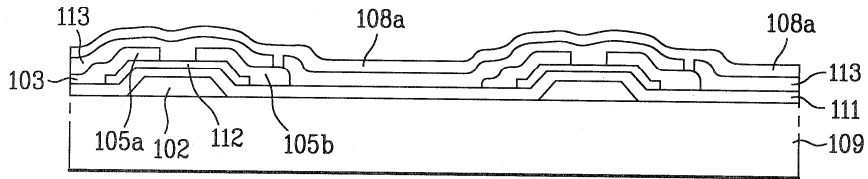
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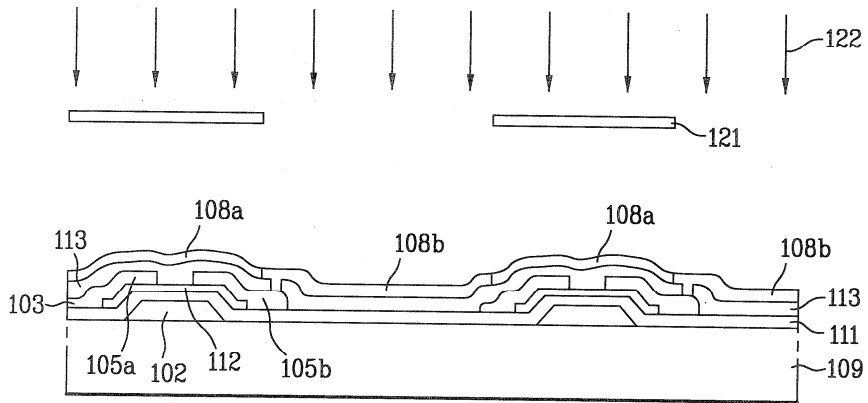
2f



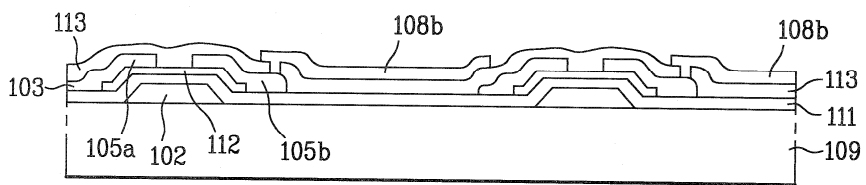
3a



3b



3c



4

